What is claimed is

1. A sputtering target containing Co and Pt as metal components, wherein a molar ratio of a content of Pt to a content of Co is from ~~5~~19/100 to ~~45~~43/100, and wherein the sputtering target contains Nb_2O_5 and TiO_2 as a metal oxide component~~s.~~.

~~2. The sputtering target according to claim 1,~~ wherein the sputtering target has a content of Nb_2O_5 of from 0.5 mol% to 5 mol~~%.~~%, and wherein the sputtering target contains 3.6 mol% or less of Cr or is free of Cr.

2. The sputtering target according to claim 1, wherein the sputtering target further contains B_2O_3 as a metal oxide component.

3. The sputtering target according to claim 1 or 2, wherein the sputtering target further contains SiO_2~~TiO_2~~ as a metal oxide component.

4. The sputtering target according to claim 3, wherein the sputtering target has a content of TiO_2 of from 0.5 mol% to 15 mol%.

5. The sputtering target according to any one claim~~s 3~~ 1 or 4, wherein the sputtering target has ~~a phase including all of Ti, Nb and O.~~ a total content of metal oxides including Nb_2O_5 of from 20 vol% to 40 vol%.

6. The sputtering target according to any one of claims 1 to 5, wherein the sputtering target ~~further~~ contains ~~at least one metal oxide of SiO_2 and B_2O_3 as a metal oxide component, and wherein the sputtering target has a total content of metal oxides including Nb_2O_5 of from 20 vol% to 40 vol%.~~Pt in an amount of from 2 mol% to 25 mol%.

7. The sputtering target according to any one of claims 1 to 6, wherein the sputtering target ~~has a molar ratio of a content of Pt to a content of Co of from 15/100 to 35/100.~~ further contains Ru as a metal component in an amount of from 0.5 mol% to 20 mol%.

~~8. The sputtering target according to any one of claims 1 to 7, wherein the sputtering target contains Pt in an amount of from 2 mol% to 25 mol%.~~

~~9. The sputtering target according to any one of claims 1 to 8, wherein the~~

~~sputtering target further contains Cr and/or Ru as a metal component(s) in an amount of from 0.5 mol% to 20 mol%.~~

~~10~~8. A method for producing a laminated film, the method comprising: forming, by sputtering using the sputtering target according to any one of claims 1 to ~~9~~7, a magnetic layer on a base layer containing Ru or on an intermediate layer formed on the base layer by sputtering using a sputtering target containing Co and at least one metal selected from the group consisting of Cr and Ru as a metal component.

~~11~~9. A laminated film, comprising: a base layer containing Ru; and a magnetic layer directly formed on the base layer or indirectly formed on the base layer via an intermediate layer containing Co and at least one metal selected from the group consisting of Cr and Ru as a metal component, the magnetic layer containing Co and Pt as metal components and having a molar ratio of a content of Pt to a content of Co ~~of from 5/100 to 45/100; wherein the magnetic layer contains Nb_2O_5 as a metal oxide component.~~ as the metal components of from 19/100 to 43/100; wherein the magnetic layer contains Nb_2O_5 and TiO_2 as metal oxide components, wherein the sputtering target has a content of Nb_2O_5 of from 0.5 mol% to 5 mol%, and wherein the sputtering target contains 3.6 mol% or less of Cr or is free of Cr.

~~12. The laminated film according to claim 11, wherein the magnetic layer further contains TiO_2 as a metal oxide component.~~

~~13~~10. A magnetic recording medium comprising the laminated film according to claim ~~11 or 12~~9.